

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

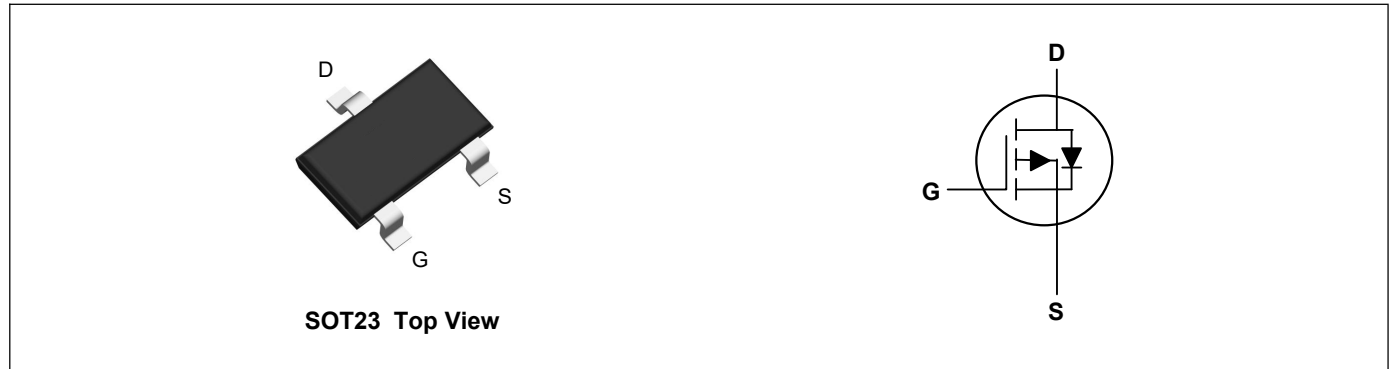
Product Summary



V_{DS}	-150	V
I_D	-1	A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	750	m Ω
$R_{DS(ON)}$ (at $V_{GS}=-6V$)	950	m Ω

Applications

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_A=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_D@T_A=25^{\circ}C$	-1	A
Continuous Drain Current ¹	$I_D@T_A=100^{\circ}C$	-0.8	A
Pulsed Drain Current ²	I_{DM}	-4	A
Total Power Dissipation ³	$P_D@T_C=25^{\circ}C$	1.56	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	80	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-150	---	---	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-1A$	---	650	750	$m\Omega$
		$V_{GS}=-6V, I_D=-0.5A$	---	700	950	$m\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-2	-3	-4	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-150V, V_{GS}=0V$	---	---	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{DS}=-10V, I_D=-1A$	---	2	---	S
Gate Resistance	R_g	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	30	---	Ω
Total Gate Charge	Q_g	$V_{DS}=-75V, V_{GS}=-10V, I_D=-1A$	---	4.4	---	nC
Gate-Source Charge	Q_{gs}		---	0.7	---	
Gate-Drain Charge	Q_{gd}		---	1.5	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=-75V, V_{GS}=-10V, R_G=10\Omega, I_D=-1A$	---	12.5	---	ns
Rise Time	T_r		---	8.8	---	
Turn-Off Delay Time	$T_{d(off)}$		---	17	---	
Fall Time	T_f		---	11	---	
Input Capacitance	C_{iss}	$V_{DS}=-25V, V_{GS}=0V, f=1MHz$	---	425	---	pF
Output Capacitance	C_{oss}		---	38	---	
Reverse Transfer Capacitance	C_{rss}		---	28	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ¹	I_S		---	---	-1	A
Diode Forward Voltage ²	V_{SD}	$V_{GS}=0V, I_S=-1A, T_J=25^{\circ}\text{C}$	---	---	-1	V

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150 $^{\circ}\text{C}$ junction temperature

Typical Characteristics

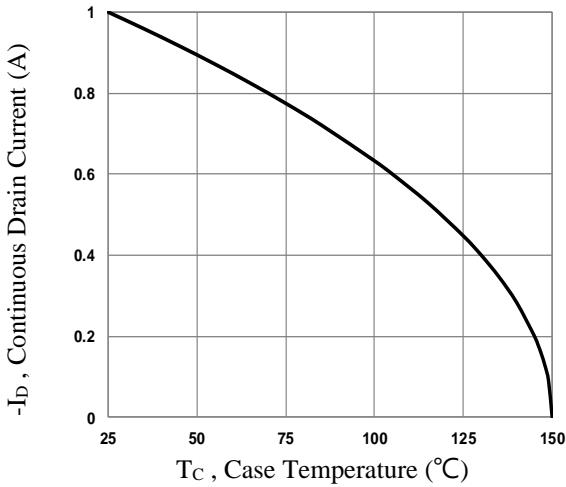


Fig.1 Continuous Drain Current vs. T_c

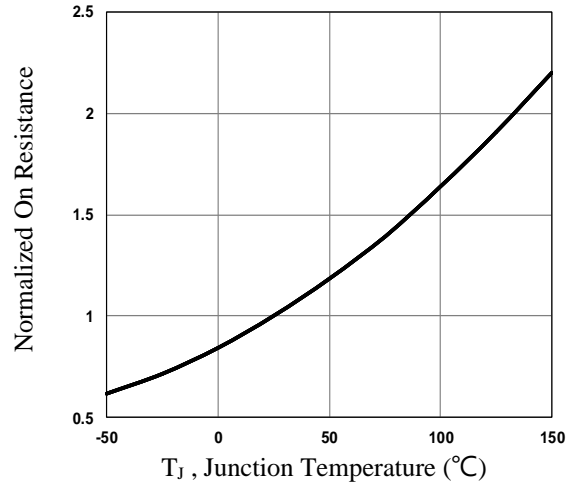


Fig.2 Normalized R_{DS(on)} vs. T_j

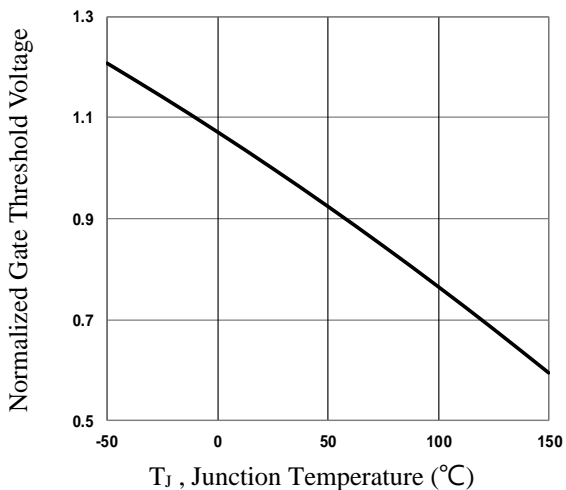


Fig.3 Normalized V_{th} vs. T_j

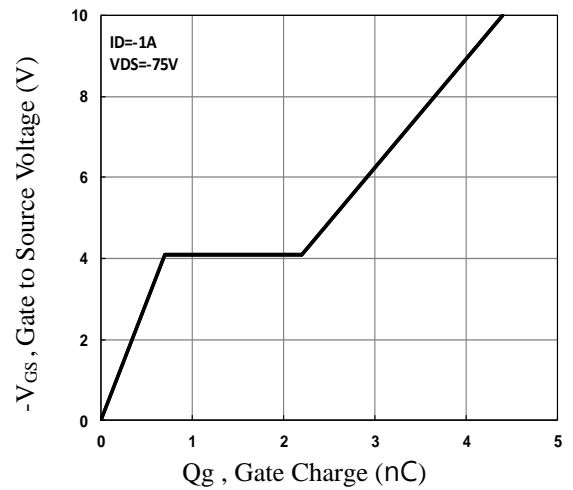


Fig.4 Gate Charge Waveform

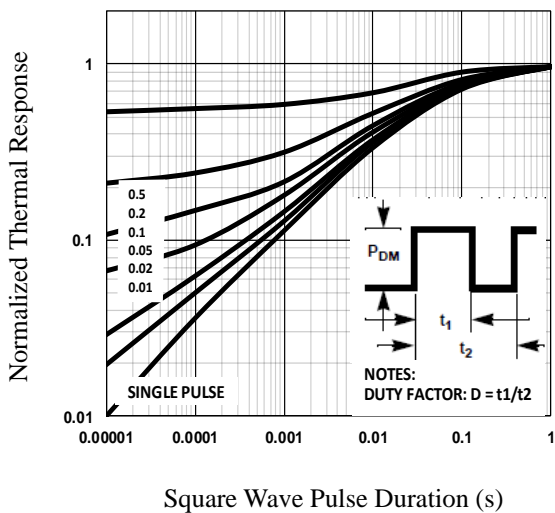


Fig.5 Normalized Transient Impedance

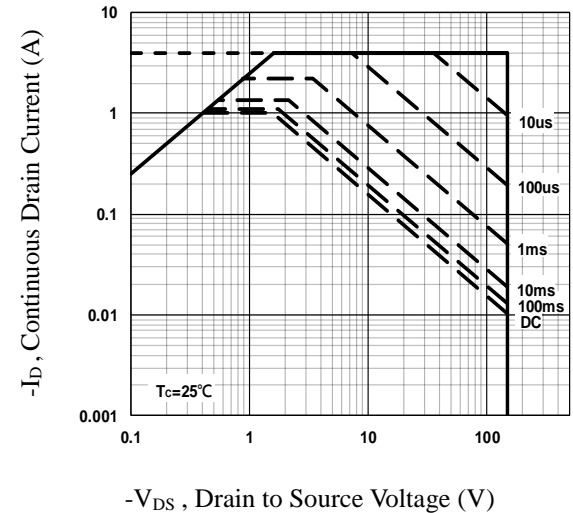


Fig.6 Maximum Safe Operation Area

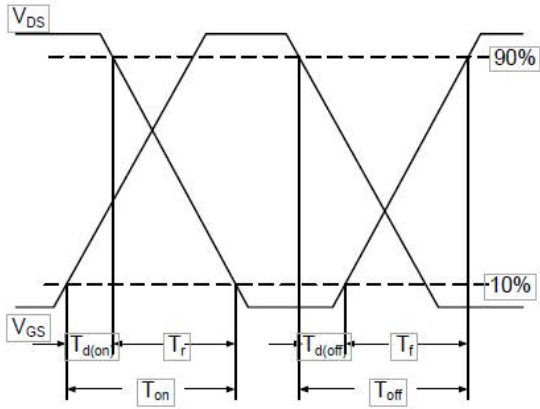


Fig.7 Switching Time Waveform

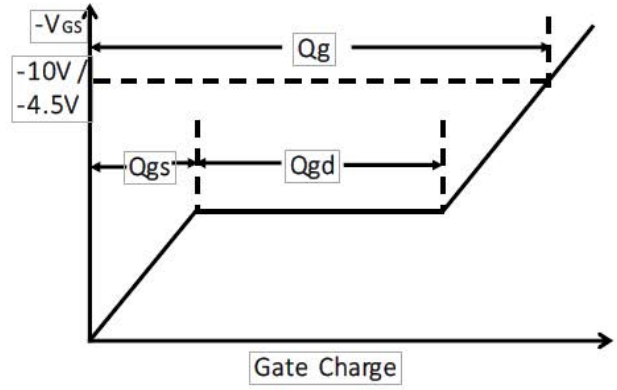


Fig.8 Gate Charge Waveform

SOT23 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.90	1.05	1.20	e₁	--	0.95	--
A₁	0.01	0.05	0.10	H_E	2.10	2.40	2.50
b_p	0.38	0.42	0.48	L_p	0.40	0.50	0.60
c	0.09	0.13	0.15	Q	0.45	0.49	0.55
D	2.80	2.92	3.00	V	--	0.20	--
E	1.20	1.33	1.40	W	--	0.10	--
e	--	1.90	--				